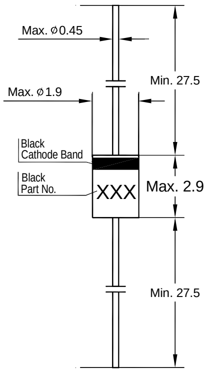
MA700B

SILICON SCHOTTKY BARRIER DIODE



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	20	V
Power Dissipation	P_{tot}	400 [1]	mW
Peak Surge Curent (Single Cycle 60 Hz Sine Wave)	I_{FSM}	15	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{Stg}	- 55 to + 175	°C
[1] Valid provided that electrodes are kept at ambient temperature.			

Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 90 mA	V_F	-	1	V
Reverse Leakage Current at V_R = 20 V	I_R	-	30	µA
Junction Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	50	-	pF
Reverse Recovery Time at I_F = I_R = 5 mA to 200 mA , recover to 0.1 I_R	t_{rr}	10	-	ns

Dated : 25/06/2007